

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

G00002

(19) World Intellectual Property Organization
International Bureau(43) International Publication Date
6 June 2002 (06.06.2002)

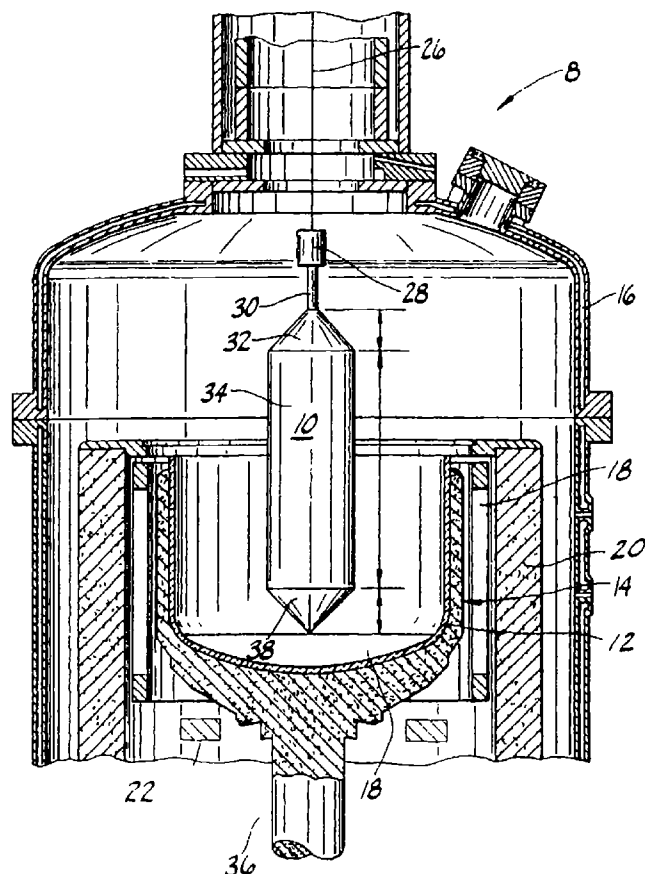
PCT

(10) International Publication Number
WO 02/044446 A3

- (51) International Patent Classification⁷: C30B 29/06, 15/00, 15/14
- (21) International Application Number: PCT/US01/44180
- (22) International Filing Date:
26 November 2001 (26 11.2001)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
2000-364601 30 November 2000 (30.11.2000) JP
2000-374147 8 December 2000 (08 12.2000) JP
60/273,980 7 March 2001 (07.03.2001) US
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- (81) Designated States (national): CN, KR, SG, US.
- (84) Designated States (regional): European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE, TR)
- Published:
— with international search report

[Continued on next page]

(54) Title: PROCESS FOR CONTROLLING THERMAL HISTORY OF VACANCY-DOMINATED, SINGLE CRYSTAL SILICON



(57) Abstract: A Czochralski method of producing a single crystal silicon ingot having a uniform thermal history. In the process, the power supplied to the side heater is decreased during the growth of a latter portion of main body, and optionally the end-cone, of the ingot, while power supplied to a bottom heater is gradually increased during growth the same portion. The present process enables a substantial portion of an ingot to be obtained yielding wafers having fewer light point defects in excess of about 0.2 microns and improved gate oxide integrity.

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(88) Date of publication of the international search report:
16 January 2003

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette